

CSD19536KTT 100V N-Channel NexFET™ Power MOSFET

1 Features

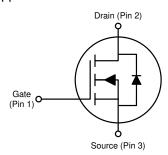
- Ultra-low Q_g and Q_{gd} Low thermal resistance
- Avalanche rated
- Lead-free terminal plating
- RoHS compliant
- Halogen free
- D²PAK plastic package

2 Applications

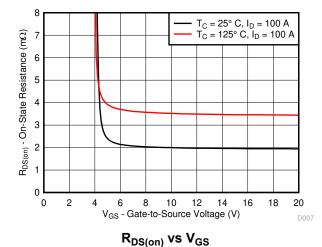
- Secondary side synchronous rectifier
- Hot swap
- Motor control

3 Description

This 100V, $2m\Omega$, D^2PAK (TO-263) $NexFET^{\text{TM}}$ power MOSFET is designed to minimize losses in power conversion applications.



Pin Out



Product Summary

$T_A = 25$	°C	TYPICAL VA	UNIT	
V _{DS}	Drain-to-Source Voltage	ource Voltage 100		V
Q_g	Gate Charge Total (10V) 118		118	
Q_{gd}	Gate Charge Gate-to-Drain	17		nC
D	Drain-to-Source On-	V _{GS} = 6V	2.2	mΩ
DS(on)	Resistance	V _{GS} = 10V	2	11152
V _{GS(th)}	Threshold Voltage	2.5	V	

Device Information

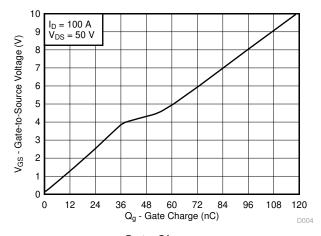
DEVICE ⁽¹⁾	QTY	MEDIA	PACKAGE	SHIP
CSD19536KTT	500	13-Inch	D ² PAK Plastic	Tape and Reel
CSD19536KTTT	50	Reel	Package	Tape and Neer

For all available packages, see the orderable addendum at the end of the data sheet.

Absolute Maximum Ratings

T _A = 2	5°C	VALUE	UNIT
V _{DS}	Drain-to-Source Voltage	100	V
V _{GS}	Gate-to-Source Voltage	±20	V
	Continuous Drain Current (Package Limited)	200	
I _D	Continuous Drain Current (Silicon Limited), T _C = 25°C	272	Α
	Continuous Drain Current (Silicon Limited), T _C = 100°C	192	
I _{DM}	Pulsed Drain Current ⁽¹⁾	400	Α
P _D	Power Dissipation	375	W
T _J , T _{stg}	Operating Junction, Storage Temperature	-55 to 175	°C
E _{AS}	Avalanche Energy, Single Pulse I_D = 127A, L = 0.1mH, R_G = 25 Ω	806	mJ

Max $R_{\theta JC}$ = 0.4°C/W, Pulse duration ≤ 100 μ s, Duty cycle ≤



Gate Charge



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4 Specifications

4.1 Electrical Characteristics

T_A = 25°C (unless otherwise stated)

	PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
STATIC	CHARACTERISTICS		<u>'</u>		
BV _{DSS}	Drain-to-source voltage	V _{GS} = 0V, I _D = 250μA	100		V
I _{DSS}	Drain-to-source leakage current	V _{GS} = 0V, V _{DS} = 80V		1	μA
I _{GSS}	Gate-to-source leakage current	V _{DS} = 0V, V _{GS} = 20V		100	nA
V _{GS(th)}	Gate-to-source threshold voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2.1 2.5	3.2	V
D	Drain-to-source on-resistance	V _{GS} = 6V, I _D = 100A	2.2	2.8	mΩ
R _{DS(on)}	Drain-to-source on-resistance	V _{GS} = 10V, I _D = 100A	2	2.4	11112
g _{fs}	Transconductance	V _{DS} = 10V, I _D = 100A	329		S
DYNAM	IC CHARACTERISTICS			,	
C _{iss}	Input capacitance		9250	12000	pF
C _{oss}	Output capacitance	V _{GS} = 0V, V _{DS} = 50V, <i>f</i> = 1MHz	1820	2370	pF
C _{rss}	Reverse transfer capacitance		47	61	pF
R _G	Series gate resistance		1.4	2.8	Ω
Q _g	Gate charge total (10V)		118	153	nC
Q _{gd}	Gate charge gate-to-drain	V _{GS} = 0V, V _{DS} = 50V, f = 1MHz V _{DS} = 50V, I _D = 100A	17		nC
Q _{gs}	Gate charge gate-to-source	V _{DS} = 50V, I _D = 100A	37		nC
Q _{g(th)}	Gate charge at V _{th}		24		nC
Q _{oss}	Output charge	V _{DS} = 50V, V _{GS} = 0V	335		nC
t _{d(on)}	Turnon delay time		13		ns
t _r	Rise time	V _{DS} = 50V, V _{GS} = 10V,	8		ns
t _{d(off)}	Turnoff delay time	$I_{DS} = 100A$, $R_G = 0\Omega$	32		ns
t _f	Fall time		6		ns
DIODE (CHARACTERISTICS		<u> </u>	1	
V _{SD}	Diode forward voltage	I _{SD} = 100A, V _{GS} = 0V	0.9	1.1	V
Q _{rr}	Reverse recovery charge	V _{DS} = 50V, I _F = 100A,	548		nC
t _{rr}	Reverse recovery time	di/dt = 300A/μs	103		ns

4.2 Thermal Information

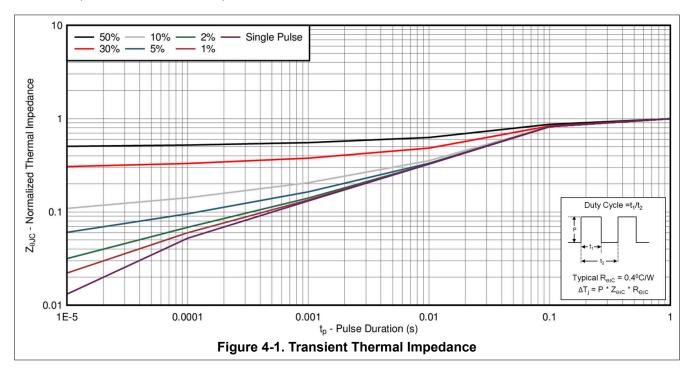
 $T_A = 25$ °C (unless otherwise stated)

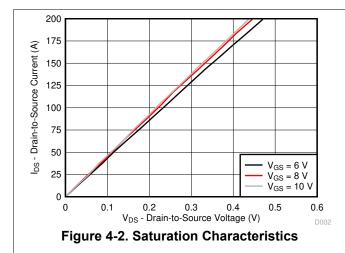
	THERMAL METRIC	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction-to-case thermal resistance			0.4	°C/W
$R_{\theta JA}$	Junction-to-ambient thermal resistance			62	°C/W

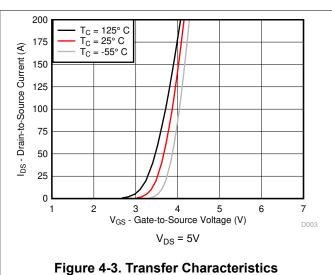


4.3 Typical MOSFET Characteristics

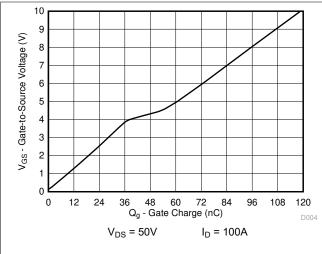
 $T_A = 25$ °C (unless otherwise stated)

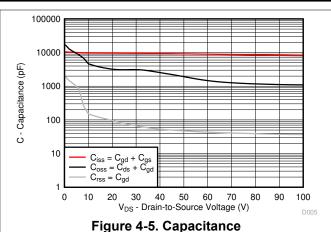






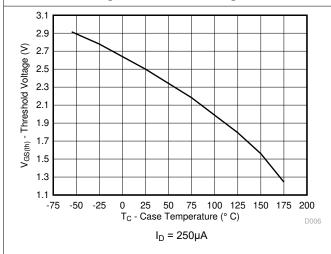
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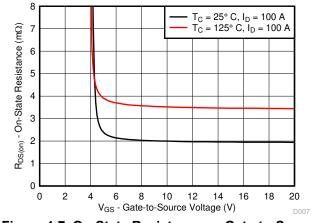
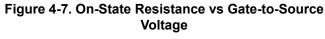
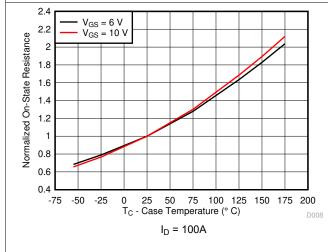


Figure 4-6. Threshold Voltage vs Temperature





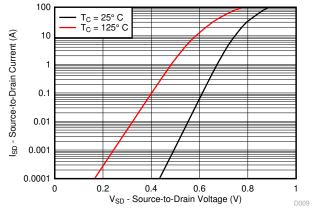


Figure 4-8. Normalized On-State Resistance vs
Temperature

Figure 4-9. Typical Diode Forward Voltage



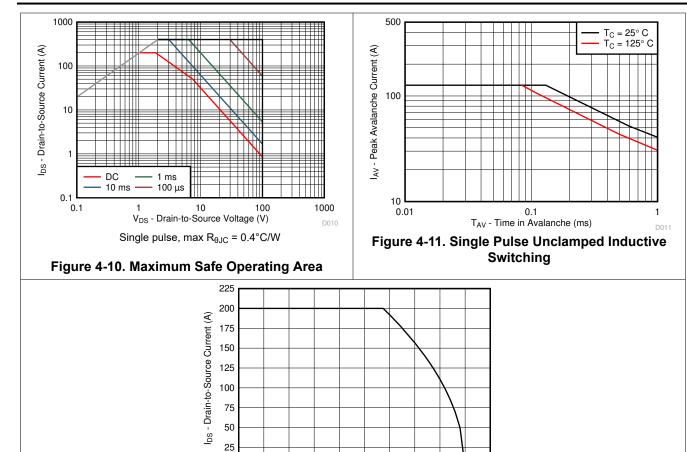


Figure 4-12. Maximum Drain Current vs Temperature

-25

-50

25 50 75 100 125 T_C - Case Temperature (° C)

150



5 Device and Documentation Support

5.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

5.2 Community Resources

5.3 Trademarks

 $\text{NexFET}^{\text{\tiny{TM}}} \text{ is a trademark of Texas Instruments}.$

All trademarks are the property of their respective owners.

6 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision B (May 2015) to Revision C (May 2025)				
Updated the numbering format for tables, figures, and cross-references throughout the	document1			
Changes from Revision A (May 2015) to Revision B (August 2016)	Page			
Added Section 5.1 section	7			
Changes from Revision * (March 2015) to Revision A (May 2015)	Page			
Added Section 5.2 section	7			
Added PCB and stencil drawings in Section 7				



7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

www.ti.com 23-May-2025

PACKAGING INFORMATION

Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
						(4)	(5)		
CSD19536KTT	Active	Production	DDPAK/ TO-263 (KTT) 2	500 LARGE T&R	ROHS Exempt	SN	Level-2-260C-1 YEAR	-55 to 175	CSD19536KTT
CSD19536KTT.B	Active	Production	DDPAK/ TO-263 (KTT) 2	500 LARGE T&R	ROHS Exempt	SN	Level-2-260C-1 YEAR	-55 to 175	CSD19536KTT
CSD19536KTTT	Active	Production	DDPAK/ TO-263 (KTT) 2	50 SMALL T&R	ROHS Exempt	SN	Level-2-260C-1 YEAR	-55 to 175	CSD19536KTT
CSD19536KTTT.B	Active	Production	DDPAK/ TO-263 (KTT) 2	50 SMALL T&R	ROHS Exempt	SN	Level-2-260C-1 YEAR	-55 to 175	CSD19536KTT

⁽¹⁾ Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.



PACKAGE OPTION ADDENDUM

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION



TAPE DIMENSIONS KO P1 BO W Cavity A0

A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	` ,	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD19536KTT	DDPAK/ TO-263	KTT	2	500	330.0	24.4	10.8	16.3	5.11	16.0	24.0	Q2
CSD19536KTTT	DDPAK/ TO-263	KTT	2	50	330.0	24.4	10.8	16.3	5.11	16.0	24.0	Q2

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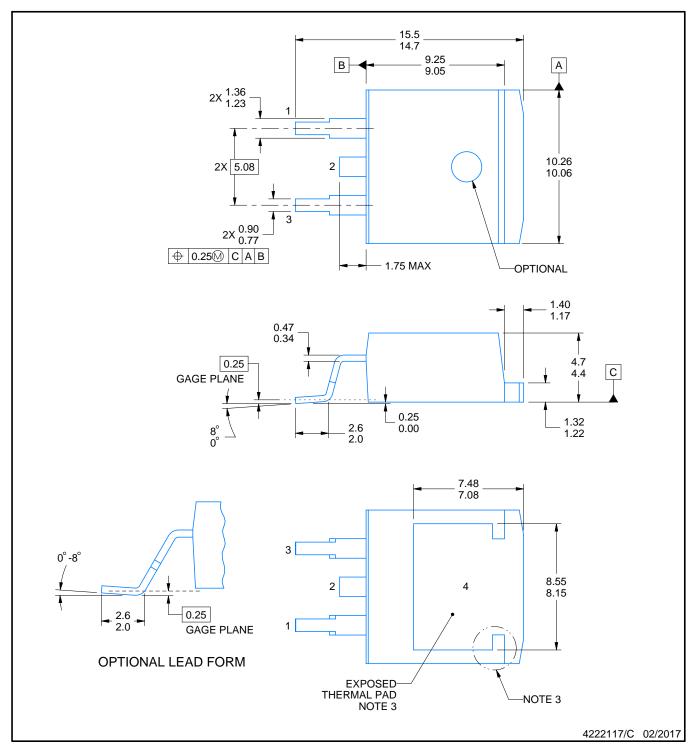


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD19536KTT	DDPAK/TO-263	ктт	2	500	340.0	340.0	38.0
CSD19536KTTT	DDPAK/TO-263	KTT	2	50	340.0	340.0	38.0



TO-263



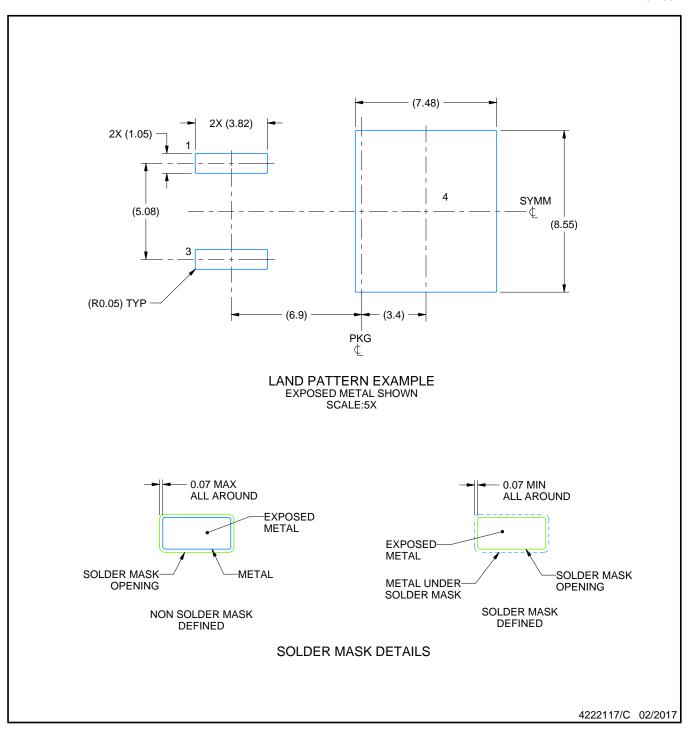
NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.
- Features may not exist and shape may vary per different assembly sites.
 Reference JEDEC registration TO-263.



TO-263

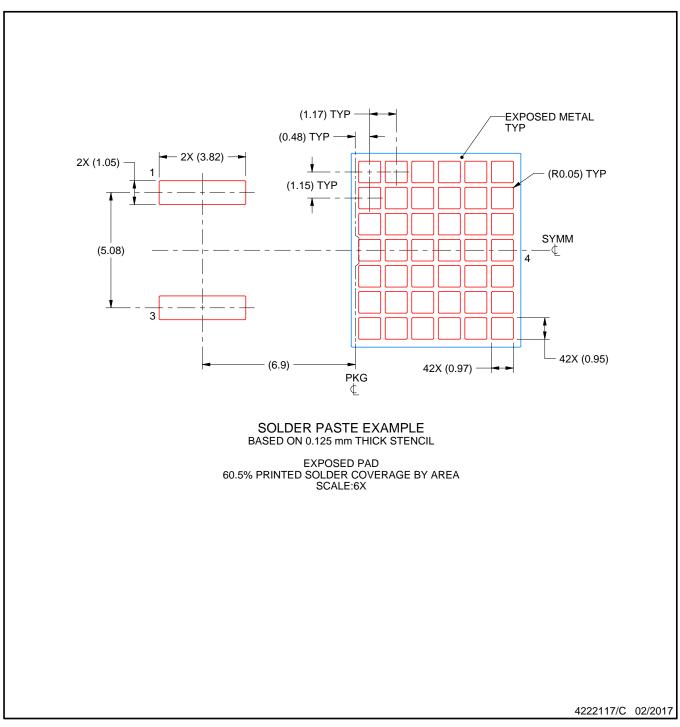


NOTES: (continued)

- 5. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature numbers SLMA002(www.ti.com/lit/slma004) and SLMA004 (www.ti.com/lit/slma004).
- 6. Vias are optional depending on application, refer to device data sheet. It is recommended that vias under paste be filled, plugged or tented.



TO-263



NOTES: (continued)

- 7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

 8. Board assembly site may have different recommendations for stencil design.



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